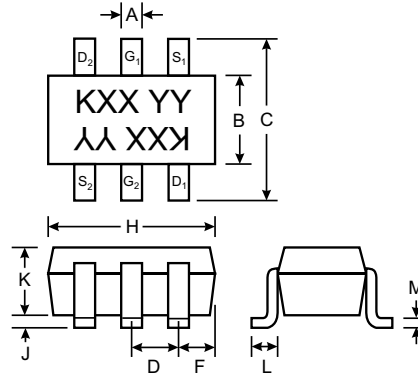


Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: KXX: Product marking code
YY: Date code
- Marking Code: K38
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	BSS138DW	Units
Drain-Source Voltage	V _{DSS}	50	V
Drain-Gate Voltage (Note 3)	V _{DGR}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 1)	I _D	200	mA
Total Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	75	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	0.5	1.2	1.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Forward Transconductance	g _{FS}	100	—	—	mS	V _{DS} =25V, I _D = 0.2A, f = 1.0KHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	50	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	8.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	—	20	ns	V _{DD} = 30V, I _D = 0.2A, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	—	20	ns	

Note: 1. Valid provided that terminals are kept at specified ambient temperature.

2. Pulse width ≤ 300μs, duty cycle ≤ 2%.

3. R_{GS} ≤ 20KΩ.